

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

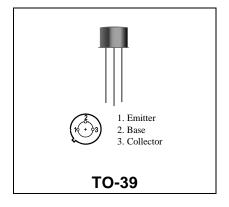
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2N6255

RF & MICROWAVE DISCRETE LOW POWER TRANSISTORS

Features

- Silicon NPN, To-39 packaged VHF Transistor
- 3.0 Watt Power Output @ 175 MHz
- Power Gain, G_{PE} = 7.8 dB
- Efficiency = 50%



DESCRIPTION:

The 2N6255 is a silicon NPN transistor, designed for 12.5 volt VHF equipment. Applications include amplifier, pre-driver, driver, and output stages. It is also suitable for oscillator and frequency-multiplier functions.

ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

| Symbol | Parameter | Value | Unit | | |
|------------------|---------------------------------------|-------|------|--|--|
| V _{CEO} | V _{CEO} Collector-Emitter 18 | | | | |
| V _{CBO} | Collector-Base Voltage | 36 | Vdc | | |
| V _{EBO} | Emitter-Base Voltage | 4.0 | Vdc | | |
| Ic | Collector Current | 1 | Α | | |

Thermal Data

| mormar bata | mormar bata | | | | | | |
|-------------|--|------|----------------|--|--|--|--|
| PD | Total Device Dissipation @ T _A = 25°C | 5.0 | Watts | | | | |
| | Derate above 25°C | 28.5 | mW/ ° C | | | | |



2N6255

ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

(off)

| Symbol | Test Conditions | | Value | | l lmi4 |
|--------|--|------|-------|------|--------|
| Symbol | rest Conditions | Min. | Тур. | Max. | Unit |
| BVCES | Collector-Emitter Breakdown Voltage (IC = 5.0 mAdc, VBE =0Vdc) | 36 | - | - | Vdc |
| BVCEO | Collector-Emitter Breakdown Voltage (IC=10 mAdc, IB=0) | 18 | - | - | Vdc |
| BVEBO | Emitter-Base Breakdown Voltage (IE = 1.0 mAdc, IC = 0) | 4.0 | - | | Vdc |
| ICES | Collector Cutoff Current (VCE = 15 Vdc, VBE = 0 Vdc) | - | - | 5.0 | mA |
| ICBO | Emitter Cutoff Current (VCB = 15 Vdc, IE = 0) | - | - | .25 | mA |
| (on) | | | | | |
| HFE | DC Current Gain (IC = 250 mAdc, VCE = 5.0 Vdc) | 5.0 | - | - | - |

DYNAMIC

| Symbol | Test Conditions | Value | | | |
|--------|---|-------|----|----|----|
| СОВ | Output Capacitance (VCB = 12.5Vdc, f = 1.0 MHz | - | 15 | 20 | pF |

FUNCTIONAL

| Symbol | Too | t Conditions | Value | | l lmit | |
|-----------------|------------------------|---|-------|------|--------|------|
| Symbol | Symbol Test Conditions | | Min. | Тур. | Max. | Unit |
| G _{PE} | Power Gain | Test Circuit-Figure 1 Pout = 3.0 W, VCC = 12.5Vdc f = 175 MHz | 7.8 | - | - | dB |
| ης | Collector Efficiency | Test Circuit-Figure 1 Pout = 3.0 W, VCC = 12.5Vdc f = 175 MHz | 50 | - | - | % |





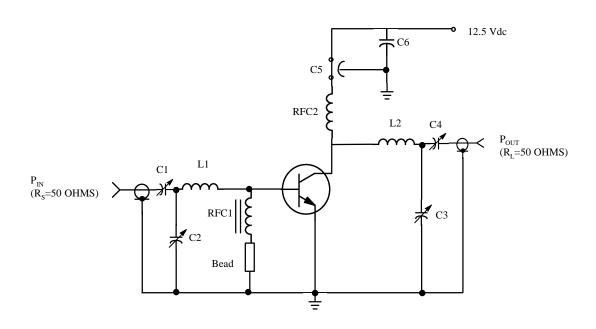


Figure 1 - 175 MHz RF AMPLIFIER CIRCUIT FOR G_{PE}, AND EFFICIENCY SPECIFICATIONS.

C1,3: 2.0-50 pF ARCO 461 ELEMENCO C2,4: 5.0-80 pF ARCO 462 ELEMENCO

C5: 1000 pF FEED THRU C6: 5.0 uF

L1: 1 TURN #18 AWG ¼" I.D.

RFC2: 0.15 uH MOLDED CHOKE

L2: 2 1/2 TURNS #18 AWG ¼" I.D

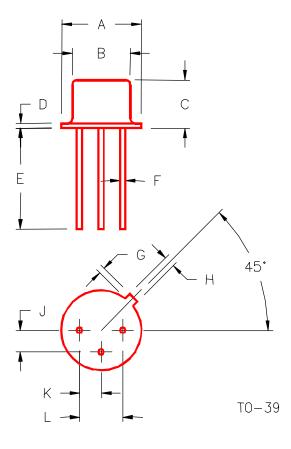
BEAD: FERROXCUBE 56-570-65/3B

RFC1: 0.15 uH MOLDED CHOKE WITH BEAD ON GROUND LEG





PACKAGE STYLE M246



| | MINIMUM | MAXIMUM | | MINIMUM | MAXIMUM |
|---|-----------|-----------|---|-----------|-----------|
| | INCHES/MM | INCHES/MM | | INCHES/MM | INCHES/MM |
| Α | .350/8,89 | .370/9,40 | J | .095/2,41 | .105/2,67 |
| В | .315/8,00 | .335/8,51 | K | .095/2,41 | .105/2,67 |
| С | .240/6,10 | .260/6,60 | L | .190/4,83 | .210/5,33 |
| D | .015/0,38 | .045/1,14 | | | |
| E | .500/ | 12,70 | | | |
| F | .016/0,41 | .019/0,48 | | | |
| G | .029/0,74 | .040/1,02 | | | |
| Н | .028/0,71 | .034/0,86 | | | |